

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 10 A, 1200 V, D1, Die

## PCFFS10120AF

### Description

Silicon Carbide (SiC) Schottky Diode has no switching loss, provides improved system efficiency against Si diodes by utilizing new semiconductor material – Silicon Carbide, enables higher operating frequency, and helps increasing power density and reduction of system size/cost. Its high reliability ensures robust operation during surge or over-voltage conditions.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 105 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

### Applications

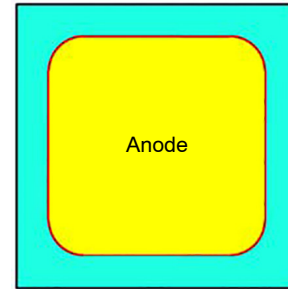
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

### Die Information

- Wafer Diameter: 6 inch
- Die Size: 2,280 × 2,280 μm (Include Scribe Lane)
- Metallization
  - ♦ Top: Ti / TiN / Al 4 μm
  - ♦ Back: Ti/ NiV / Ag
- Die Thickness: Typ. 200 μm
- Bonding Pad Size
  - ♦ Anode: 1700 × 1700 μm
- Recommended Wire Bond (Note 1)
  - ♦ Anode: 15 mil × 1

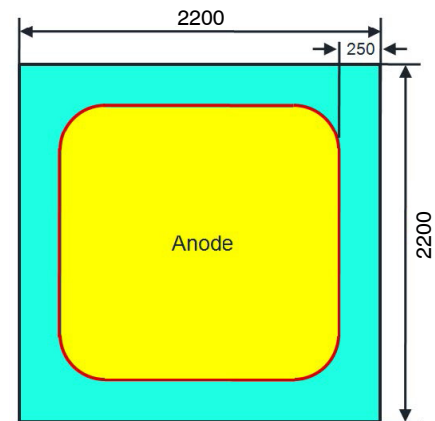
### NOTE:

1. Based on TO-247 package of onsemi



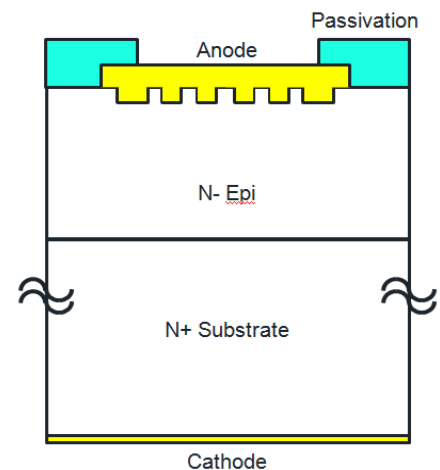
### DIE LAYOUT

(Dimension: μm, Except Scribe Lane)



- Passivation Area
- Passivation Information
  - Passivation Material: Polyimide (PSPi)
  - Passivation Type: Local Passivation
  - Passivation Thickness: 90KA

### CROSS SECTION



### ORDERING INFORMATION

Part Number	Package	Die Size
PCFFS10120AF	N/A	2,280 × 2,280 μm (Include Scribe Lane)

# PCFFS10120AF

## ELECTRICAL CHARACTERISTICS ON WAFER ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
$V_R$	Reverse Blocking Voltage	$I_R = 200 \mu\text{A}$ , $T_C = 25^\circ\text{C}$	1230	-	-	V
$V_F$	Forward Voltage	$I_F = 10 \text{ A}$ , $T_C = 25^\circ\text{C}$	1.22	-	1.723	V
$I_R$	Reverse Current	$V_R = 1230 \text{ V}$ , $T_C = 25^\circ\text{C}$	-	-	200	$\mu\text{A}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Tested 100% on wafer

3. -F: sawn-on-film frame packing based on wafer tested

## For Additional Product Information and Electrical Characteristics on Package

Refer to the [FESH20120ADN-F155](#) product datasheet.

## The Configuration of Chips (Based on 6 Inch Wafer)

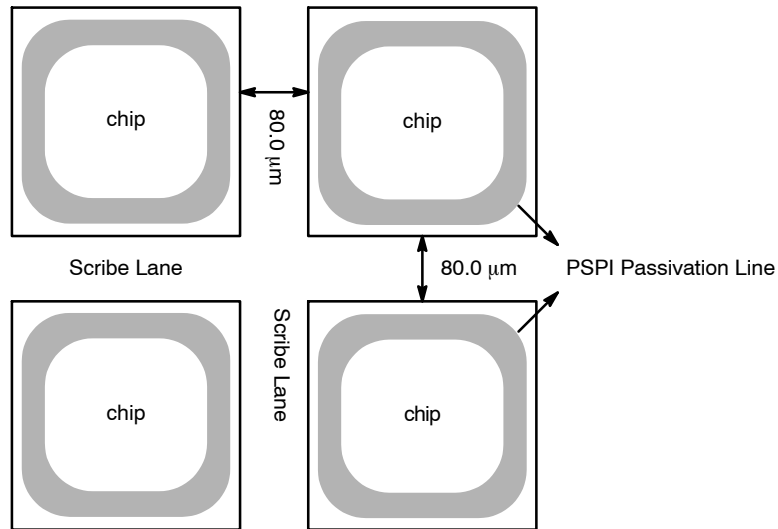


Figure 1. The Configuration of Chips (Based on 6 Inch Wafer)

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